



PATENT
Attorney Docket No. ASC-022CPC1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Wu et al.
SERIAL NO.: 10/603,852 GROUP NO.: 2811
FILING DATE: June 25, 2003 EXAMINER: Douglas Owens
TITLE: ETCH STOP LAYER SYSTEM

Mail Stop ISSUE FEE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

The references listed on the enclosed Form PTO/SB/08 are submitted solely in compliance with the duty of candor. It is understood that this Information Disclosure Statement does not fall within the provisions of 37 C.F.R. §1.97. Copies of cited non-patent literature numbered C176-C196 are enclosed.

It is respectfully requested that the references listed on the attached Form PTO/SB/08, and other information contained herein, be made of record in this application.

Respectfully submitted,

Date: April 3, 2007
Reg. No. 44,381

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Substitute for form 1449/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

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| Sheet | 1 | of | 2 | Attorney Docket Number | ASC-022CPC1 |
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Complete if Known

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| Application Number | 10/603,852 |
| Filing Date | June 25, 2003 |
| First Named Inventor | Eugene A. Fitzgerald |
| Art Unit | 2811 |
| Examiner Name | D. W. Owens |
| Attorney Docket Number | ASC-022CPC1 |

U.S. PATENT DOCUMENTS

| Examiner Initials | Cite No. ¹ | Document Number | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
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| | | Country Code ³ -Number ⁴ -Kind Code ⁵ (if known) | | | | |
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. CITE NO.: Those application(s) which are marked with a single asterisk (*) next to the Cite No. are not supplied (under 37 CFR 1.98(a)(2)(iii)) because that application was filed after June 30, 2003 or is available in the IFW. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS

| Examiner Initials | Cite No. ¹ | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T ² |
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